

1.2V Drive Nch MOSFET

RUE002N05

●Structure

Silicon N-channel MOSFET

●Features

- 1) High speed switing.
- 2) Small package(EMT3).
- 3) Ultra low voltage drive(1.2V drive).

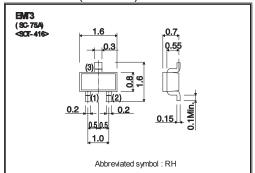
Application

Switching

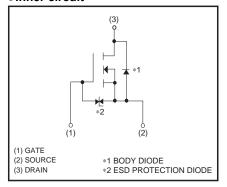
Packaging specifications

| | Package | Taping | |
|----------|------------------------------|--------|--|
| Type | Code | TL | |
| | Basic ordering unit (pieces) | 3000 | |
| RUE002N0 | 0 | | |

●Dimensions (Unit : mm)



•Inner circuit



●Absolute maximum ratings (Ta = 25°C)

| Parame | Symbol | Limits | Unit | |
|------------------------------|------------|--------------------|-------------|----|
| Drain-source voltage | | V_{DSS} | 50 | V |
| Gate-source voltage | | V_{GSS} | ±8 | V |
| Drain current | Continuous | I_D | ±200 | mΑ |
| | Pulsed | I _{DP} *1 | ±800 | mΑ |
| Source current | Continuous | I _S | 125 | mA |
| (Body Diode) | Pulsed | I _{SP} *1 | 800 | mA |
| Power dissipation | | P _D *2 | 150 | mW |
| Channel temperature | | Tch | 150 | °C |
| Range of storage temperature | | Tstg | -55 to +150 | °C |

^{*1} Pw≤10µs, Duty cycle≤1%

Thermal resistance

| Parameter | Symbol | Limits | Unit |
|--------------------|-------------|--------|--------|
| Channel to ambient | Rth (ch-a)* | 833 | °C / W |

^{*} Each terminal mounted on a recommended land.

^{*2} Each terminal mounted on a recommended land.

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●Electrical characteristics (Ta = 25°C)

| Parameter | Symbol | Min. | Тур. | Max. | Unit | Conditions |
|---|------------------------|------|------|------|------|--|
| Gate-source leakage | I_{GSS} | 1 | - | ±10 | μA | $V_{GS}=\pm 8V, V_{DS}=0V$ |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | 50 | - | 1 | ٧ | I _D =1mA, V _{GS} =0V |
| Zero gate voltage drain current | I _{DSS} | 1 | - | 1 | μA | V_{DS} =50V, V_{GS} =0V |
| Gate threshold voltage | V _{GS (th)} | 0.3 | - | 1.0 | ٧ | V _{DS} =10V, I _D =1mA |
| | | 1 | 1.6 | 2.2 | | I _D =200mA, V _{GS} =4.5V |
| Static ducin course on state | | 1 | 1.7 | 2.4 | | I _D =200mA, V _{GS} =2.5V |
| Static drain-source on-state resistance | R _{DS (on)} * | 1 | 1.9 | 2.7 | Ω | I _D =100mA, V _{GS} =1.8V |
| recietarios | | 1 | 2.0 | 4.0 | | I _D =40mA, V _{GS} =1.5V |
| | | 1 | 2.4 | 7.2 | | I _D =20mA, V _{GS} =1.2V |
| Forward transfer admittance | IY _{fs} I* | 0.4 | - | - | S | I _D =200mA, V _{DS} =10V |
| Input capacitance | C _{iss} | 1 | 25 | - | pF | V _{DS} =10V |
| Output capacitance | C _{oss} | 1 | 6 | - | pF | V _{GS} =0V |
| Reverse transfer capacitance | C _{rss} | 1 | 3 | - | pF | f=1MHz |
| Turn-on delay time | t _{d(on)} * | - | 4 | - | ns | I _D =100mA, V _D ;≒ 30V |
| Rise time | t _r * | - | 6 | - | ns | V _{GS} =4.5V |
| Turn-off delay time | t _{d(off)} * | | 15 | _ | ns | R_L =300 Ω |
| Fall time | t _f * | - | 55 | - | ns | R_G =10 Ω |

^{*}Pulsed

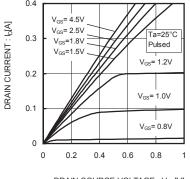
●Body diode characteristics (Source-Drain) (Ta = 25°C)

| Parameter | Symbol | Min. | Тур. | Max. | Unit | Conditions |
|-----------------|-------------------|------|------|------|------|--|
| Forward voltage | V _{SD} * | - | - | 1.2 | V | I _s =200mA, V _{GS} =0V |

^{*}Pulsed

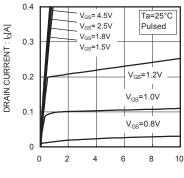
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Electrical characteristic curves



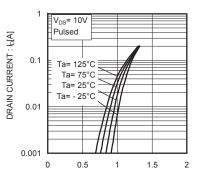
DRAIN-SOURCE VOLTAGE : VDS[V]

Fig.1 Typical Output Characteristics(I)



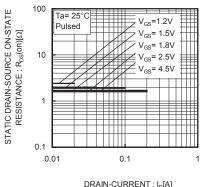
DRAIN-SOURCE VOLTAGE: VDS[V]

Fig.2 Typical Output Characteristics(II)



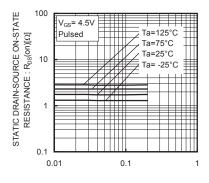
GATE-SOURCE VOLTAGE: VGS[V]

Fig.3 Typical Transfer Characteristics



DRAIN-CURRENT : $I_D[A]$

Fig.4 Static Drain-Source On-State Resistance vs. Drain Current(I)



DRAIN-CURRENT : I_D[A]

Fig.5 Static Drain-Source On-State Resistance vs. Drain Current(II)

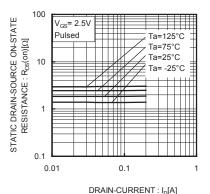


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(Ⅲ)

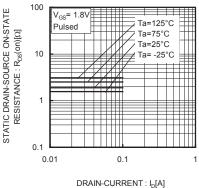


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current(IV)

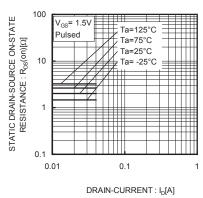


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current(V)

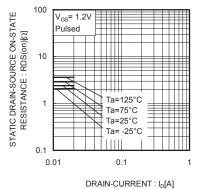
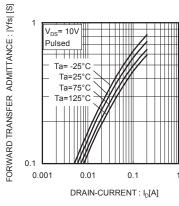
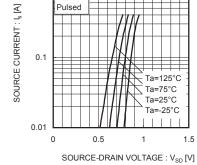


Fig.9 Static Drain-Source On-State Resistance vs. Drain Current(VI) **RUE002N05 Data Sheet**





V_{GS}=0V

Pulsed

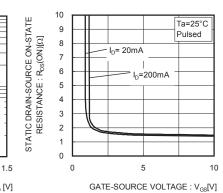
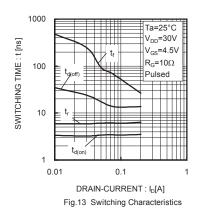
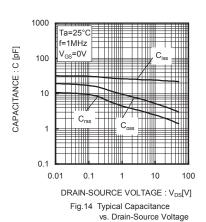


Fig.10 Forward Transfer Admittance vs. Drain Current

Fig.11 Reverse Drain Current vs. Sourse-Drain Voltage

Fig.12 Static Drain-Source On-State Resistance vs. Gate Source Voltage





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●Measurement circuits

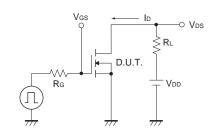


Fig.1-1 Switching time measurement circuit

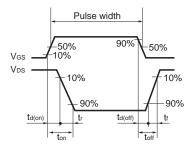


Fig.1-2 Switching waveforms

●Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

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